20-bit Universal Bus Driver with 3-state Outputs

HITACHI

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Description

This 20-bit universal bus driver is designed for 2.3 V to 3.6 V V_{CC} operation.

Data flow from A to Y is controlled by the output enable (\overline{OE}) input. The device operates in the transparent mode when the latch enable (\overline{LE}) input is low. The A data is latched if the clock (CLK) input is held at a high or low logic level. If \overline{LE} is high, the A data is stored in the latch flip flop on the low to high transition of CLK. When \overline{OE} is high, the outputs are in the high impedance state.

To ensure the high impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current sinking capability of the driver.

Active bus hold circuitry is provided to hold unused or floating inputs at a valid logic level.

Features

- $V_{CC} = 2.3 \text{ V to } 3.6 \text{ V}$
- Typical V_{OL} ground bounce < 0.8 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- Typical V_{OH} undershoot > 2.0 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- High output current ± 24 mA (@V_{CC} = 3.0 V)
- Bus hold on data inputs eliminates the need for external pullup / pulldown resistors



Function Table

Inputs				Output Y
ŌĒ	LE	CLK	Α	_
Н	X	X	X	Z
L	L	X	L	L
L	L	X	Н	Н
L	Н	\uparrow	L	L
L	Н	\uparrow	Н	Н
L	Н	Н	X	Y ₀ *1
L	Н	L	X	Y ₀ *2

H : High level

L : Low level

X : Immaterial

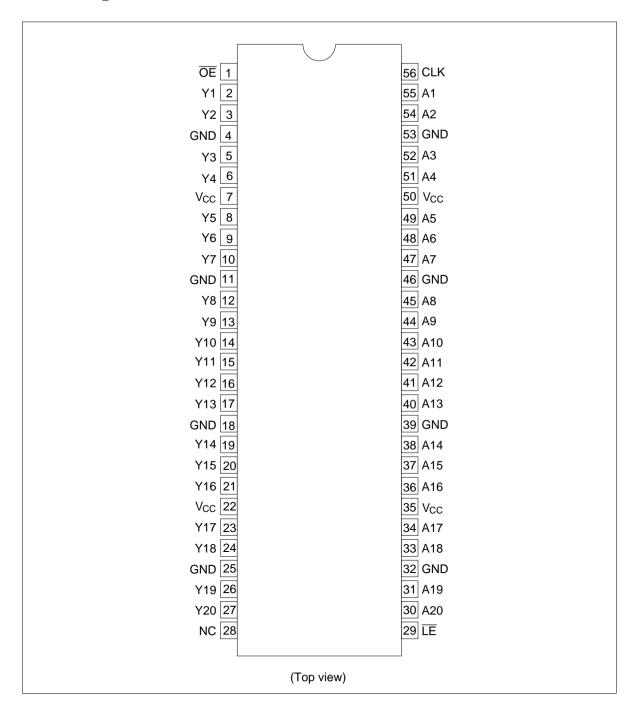
Z : High impedance

 \uparrow : Low to high transition

Notes: 1. Output level before the indicated steady state input conditions were established, provided that CLK is high before $\overline{\text{LE}}$ goes low.

2. Output level before the indicated steady state input conditions were established.

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V _{cc}	-0.5 to 4.6	V	
Input voltage *1	V _I	-0.5 to 4.6	V	
Output voltage *1, 2	Vo	-0.5 to V_{cc} +0.5	V	
Input clamp current	I _{IK}	-50	mA	V ₁ < 0
Output clamp current	I _{ok}	±50	mA	$V_o < 0 \text{ or } V_o > V_{cc}$
Continuous output current	Io	±50	mA	$V_{\rm O}$ = 0 to $V_{\rm CC}$
V _{cc} , GND current / pin	I _{CC} or I _{GND}	±100	mA	
Maximum power dissipation at Ta = 55°C (in still air) ^{'3}	P _T	1	W	TSSOP
Storage temperature	Tstg	-65 to 150	°C	

Notes:

Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.

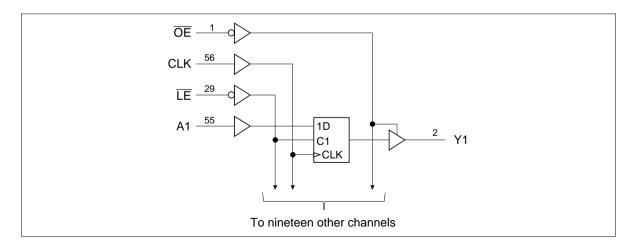
- 1. The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.
- 2. This value is limited to 4.6 V maximum.
- The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage	V _{cc}	2.3	3.6	V	
Input voltage	V_{I}	0	V_{cc}	V	
Output voltage	Vo	0	V _{cc}	V	
High level output current	I _{OH}	_	-12	mA	V _{CC} = 2.3 V
		_	-12		$V_{CC} = 2.7 \text{ V}$
		_	-24		$V_{CC} = 3.0 \text{ V}$
Low level output current	I _{OL}	_	12	mA	V _{CC} = 2.3 V
		_	12		$V_{CC} = 2.7 \text{ V}$
		_	24		$V_{CC} = 3.0 \text{ V}$
Input transition rise or fall rate	Δt / Δν	0	10	ns / V	
Operating temperature	Та	-40	85	°C	

Note: Unused control inputs must be held high or low to prevent them from floating.

Logic Diagram



Electrical Characteristics ($Ta = -40 \text{ to } 85^{\circ}\text{C}$)

Item	Symbo	I V _{cc} (V)	Min	Max	Unit	Test Conditions
Input voltage	V _{IH}	2.3 to 2.7	1.7	_	V	
		2.7 to 3.6	2.0	_	-	
	V _{IL}	2.3 to 2.7	_	0.7		
		2.7 to 3.6	_	0.8		
Output voltage	V_{OH}	2.3 to 3.6	V _{cc} -0.2	_	V	$I_{OH} = -100 \mu A$
		2.3	2.0	_	_	$I_{OH} = -6 \text{ mA}, V_{IH} = 1.7 \text{ V}$
		2.3	1.7	_	_	$I_{OH} = -12 \text{ mA}, V_{IH} = 1.7 \text{ V}$
		2.7	2.2	_	_	$I_{OH} = -12 \text{ mA}, V_{IH} = 2.0 \text{ V}$
		3.0	2.4	_	_	$I_{OH} = -12 \text{ mA}, V_{IH} = 2.0 \text{ V}$
		3.0	2.0	_	_	$I_{OH} = -24 \text{ mA}, V_{IH} = 2.0 \text{ V}$
	V _{OL}	2.3 to 3.6	_	0.2	_	$I_{OL} = 100 \mu A$
		2.3	_	0.4	_	$I_{OL} = 6 \text{ mA}, V_{IL} = 0.7 \text{ V}$
		2.3	_	0.7	_	$I_{OL} = 12 \text{ mA}, V_{IL} = 0.7 \text{ V}$
		2.7	_	0.4	_	$I_{OL} = 12 \text{ mA}, V_{IL} = 0.8 \text{ V}$
		3.0	_	0.55	_	$I_{OL} = 24 \text{ mA}, V_{IL} = 0.8 \text{ V}$
Input current	I _{IN}	3.6	_	±5	μΑ	$V_{IN} = V_{CC}$ or GND
	I _{IN (hold)}	2.3	45	_	_	V _{IN} = 0.7 V
		2.3	-45	_	_	V _{IN} = 1.7 V
		3.0	75	_	_	V _{IN} = 0.8 V
		3.0	-75	_	_	V _{IN} = 2.0 V
		3.6	_	±500	_	$V_{IN} = 0 \text{ to } 3.6 \text{ V}^{*1}$
Off state output current	l _{oz}	3.6	_	±10	μΑ	V _{OUT} = V _{CC} or GND
Quiescent supply current	I _{cc}	3.6	_	40	μΑ	$V_{IN} = V_{CC}$ or GND
	ΔI_{CC}	3.0 to 3.6	_	750	μΑ	V_{IN} = one input at (V_{CC} -0.6) V, other inputs at V_{CC} or GND

Note: 1. This is the bus hold maximum dynamic current required to switch the input from one state to another.

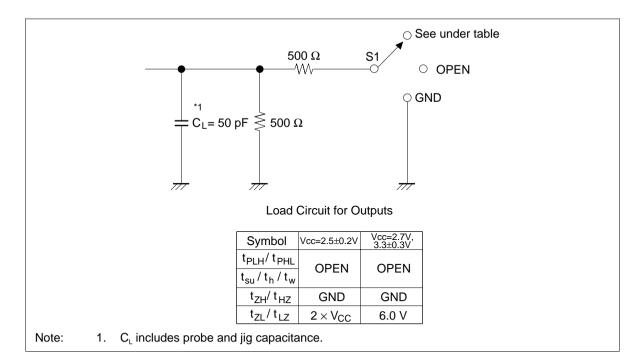
Switching Characteristics ($Ta = -40 \text{ to } 85^{\circ}\text{C}$)

Item	Symbol	V _{cc} (V)	Min	Тур	Max	Unit	FROM (Input)	TO (Output)
Maximum clock frequency	f _{max}	2.5±0.2	150	_	_	MHz		
		2.7	150	_	_			
		3.3±0.3	150	_	_			
Propagation delay time	t _{PLH}	2.5±0.2	1.0	_	4.2	ns	Α	Υ
	t_{PHL}	2.7	_	_	4.2			
		3.3±0.3	1.0	_	3.6			
		2.5±0.2	1.3	_	5.0		LE	Υ
		2.7	_	_	4.9			
		3.3±0.3	1.3	_	4.2			
		2.5±0.2	1.4	_	5.5		CLK	Υ
		2.7	_	_	5.2			
		3.3±0.3	1.4	_	4.5			
Output enable time	t _{zH}	2.5±0.2	1.4	_	5.5	ns	ŌĒ	Υ
	t_{zL}	2.7	_	_	5.6			
		3.3±0.3	1.1	_	4.6			
Output disable time	t _{HZ}	2.5±0.2	1.0	_	4.5	ns	ŌĒ	Υ
	t_{LZ}	2.7	_	_	4.3			
		3.3±0.3	1.3	_	3.9			
Input capacitance	C _{IN}	3.3	_	3.5	_	pF	Control in	outs
		3.3	_	6.0	_	_	Data input	s
Output capacitance	Co	3.3	_	7.0	_	pF	Outputs	

Switching Characteristics (Ta = -40 to 85°C) (cont)

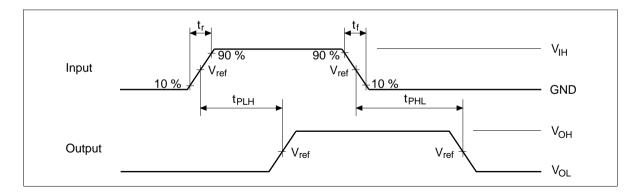
Item	Symbol	V_{cc} (V)	Min	Тур	Max	Unit	FROM (Input)
Setup time	t _{su}	2.5±0.2	1.4	_	_	ns	Data before CLK↑
		2.7	1.7	_	_		
		3.3±0.3	1.5	_	_		
		2.5±0.2	1.2	_	_		Data before LE ↑
		2.7	1.6	_	_		CLK "H"
		3.3±0.3	1.3	_	_		
		2.5±0.2	1.4	_	_		Data before LE ↑
		2.7	1.5	_	_		CLK "L"
		3.3±0.3	1.2	_	_		
Hold time	t _h	2.5±0.2	0.9	_	_	ns	Data after CLK↑
		2.7	0.9	_	_		
		3.3±0.3	0.9	_	_		
		2.5±0.2	1.1	_	_		Data after LE ↑
		2.7	1.1	_	_		CLK "H" or "L"
		3.3±0.3	1.1	_	_		
Pulse width	t_w	2.5±0.2	3.3	_	_	ns	ΙΕ "L"
		2.7	3.3	_	_		
		3.3±0.3	3.3	_	_		
		2.5±0.2	3.3	_	_		CLK "H" or "L"
		2.7	3.3	_	_		
		3.3±0.3	3.3				

Test Circuit

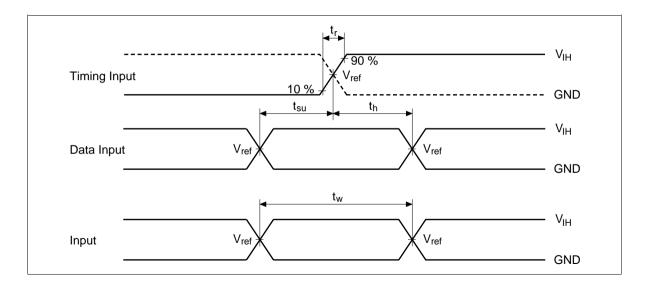


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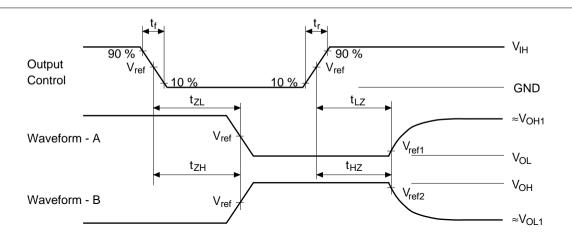
Waveforms - 1



Waveforms – 2



Waveforms - 3



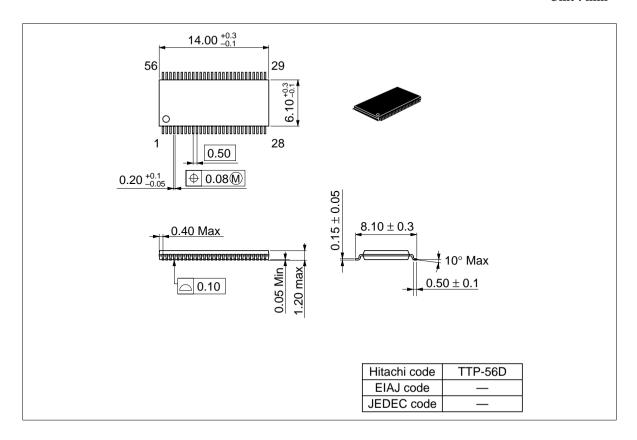
TEST	Vcc=2.5±0.2V	Vcc=2.7V, 3.3±0.3V
V _{IH}	V_{CC}	2.7 V
V _{ref}	1/2 V _{CC}	1.5 V
V _{ref1}	V _{OL} +0.15 V	V _{OL} +0.3 V
V _{ref2}	V _{OH} -0.15 V	V _{OH} -0.3 V
V _{OH1}	V _{CC}	3.0 V
V _{OL1}	GND	GND

Notes:

- 1. All input pulses are supplied by generators having the following characteristics : PRR \leq 10 MHz, Zo = 50 $\Omega,\,t_{_{f}}\leq$ 2.0 ns, $t_{_{f}}\leq$ 2.0 ns. (V $_{_{CC}}$ = 2.5±0.2 V) PRR \leq 10 MHz, Zo = 50 $\Omega,\,t_{_{f}}\leq$ 2.5 ns, $t_{_{f}}\leq$ 2.5 ns. (V $_{_{CC}}$ = 2.7 V, 3.3±0.3 V)
- 2. Waveform A is for an output with internal conditions such that the output is low except when disabled by the output control.
- 3. Waveform B is for an output with internal conditions such that the output is high except when disabled by the output control.
- 4. The output are measured one at a time with one transition per measurement.

Package Dimensions

Unit: mm



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Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose,CA 95134 Tel: <1> (408) 433-1990 Fax: <1>(408) 433-0223 Hitachi Europe GmbH Electronic components Group Dornacher Stra§e 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0

Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park

Maidenhead Berkshire SL6 8YA, United Kingdom

Tel: <44> (1628) 585000 Fax: <44> (1628) 778322

Lower Cookham Road

Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533

Hitachi Asia Ltd. Taipei Branch Office 3F, Hung Kuo Building. No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666

Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Tsim Sha Tsui, Kowloon, Hong Kong Tel: <852> (2) 735 9218

Fax: <852> (2) 730 0281 Telex: 40815 HITEC HX

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